

 Form PTO-1449 Rev. 5-8-92 S. Department of Commerce Patent and Trademark Office		Atty Docket 7408-9-442		Serial No. 09/692,211		
		Applicants: Akihiko ISHIBASHI et al.				
		Filing Date: October 20, 2000			Group Art Unit: 2812	
U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,787,104	07/28/1998	Kamiyama et al.			
FOREIGN PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
<i>Gm</i>	0 887 436	12/30/1998	EP			Full Eng
	07-235505	09/05/1995	JP			Part Eng
	08-255932	10/01/1996	JP			X
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<i>Gm</i>	Miyake et al., "Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy", pp. L1000-L1002, September 15, 1999, Jpn. J. Appl. Phys., Vol 38, Part 2, No. 9A/B					
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	Mihopoulos, et al., "A Reaction-Transport Model for AlGaN MOVPE Growth", pp. 733-739, 1998, Journal of Crystal Growth 195					
<i>Gm</i>	Lee et al., "Characteristics of InGa _x N/GaN Grown by LPMOVPE with the Variation of Growth Temperature", pp. 6-10, 1997, Journal of Crystal Growth 182					
Examiner	<i>S. M. Lom</i>		Date Considered	<i>4/1/01</i>		
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